

CLAIMS

1. A method for eliminating boron contamination in an annealed wafer, the method comprising, when annealing a silicon wafer having a surface on which a native oxide film has formed and boron of environmental origin or from chemical treatment prior to annealing has deposited, steps of carrying out temperature heat-up in a mixed gas atmosphere having a mixing ratio of hydrogen gas to an inert gas of 5% to 100% so as to remove the boron-containing native oxide film, followed by annealing in an inert gas atmosphere.

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2. The method for eliminating boron contamination in an annealed wafer according to claim 1, wherein a treatment temperature of the temperature heat-up in the mixed gas atmosphere is from 700 to 1,200°C.

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3. The method for eliminating boron contamination in an annealed wafer according to claim 1 or 2, wherein the temperature heat-up is carried out in the mixed gas atmosphere in which the mixing ration of the hydrogen gas to the inert gas is from 10% to 30%.

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